



DMP2225L

#### P-CHANNEL ENHANCEMENT MODE FIELD EFFECT TRANSISTOR

#### **Features**

Low On-Resistance:

$$\begin{split} R_{DS(ON)} < 110 m\Omega & @ V_{GS} = -4.5 V \\ R_{DS(ON)} < 225 m\Omega & @ V_{GS} = -2.5 V \end{split}$$

- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Lead Free By Design/RoHS Compliant (Note 2)
- "Green" Device (Note 4)
- Qualified to AEC-Q101 Standards for High Reliability

### **Mechanical Data**

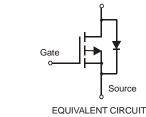
- Case: SOT-23
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020D
- Terminals: Finish Matte Tin annealed over Copper leadframe. Solderable per MIL-STD-202, Method 208
- Terminal Connections: See Diagram
- Marking Information: See Page 4
- Ordering Information: See Page 4
- Weight: 0.008 grams (approximate)

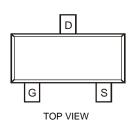
SOT-23

Drain



TOP VIEW





**Maximum Ratings** @T<sub>A</sub> = 25°C unless otherwise specified

Ch	aracteristic		Symbol	Value	Units	
Drain-Source Voltage			$V_{DSS}$	-20	V	
Gate-Source Voltage			V <sub>GSS</sub>	±12	V	
Drain Current (Note 1) Steady $T_A = 25^{\circ}C$ State $T_A = 70^{\circ}C$			I <sub>D</sub>	-2.6 -2	А	
Pulsed Drain Current (Note 3)			I <sub>DM</sub>	8	Α	

### **Thermal Characteristics**

Characteristic	Symbol	Value	Units
Total Power Dissipation (Note 1)	$P_{D}$	1.08	W
Thermal Resistance, Junction to Ambient @T <sub>A</sub> = 25°C (Note 1)	$R_{ hetaJA}$	115	°C/W
Operating and Storage Temperature Range	T <sub>J,</sub> T <sub>STG</sub>	-55 to +150	°C

Notes:

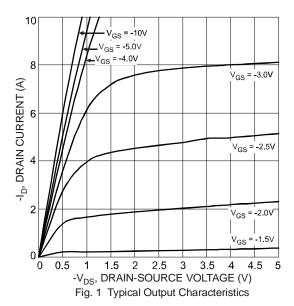
- 1. Device mounted on FR-4 PCB. t ≤5 sec.
- 2. No purposefully added lead.
- 3. Pulse width  $\leq 10 \mu S$ , Duty Cycle  $\leq 1\%$ .
- 4. Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead\_free/index.php.

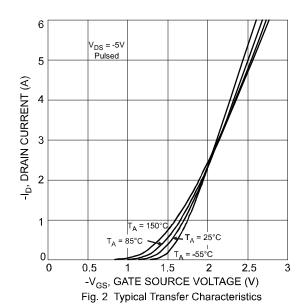


## **Electrical Characteristics** @T<sub>A</sub> = 25°C unless otherwise specified

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 5)							
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	-20			V	$V_{GS} = 0V, I_D = -250 \mu A$	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	_	_	-800	nA	$V_{DS} = -20V, V_{GS} = 0V$	
On-State Drain Current		-6	_	_	А	$V_{DS} \le -5V$ , $V_{GS} = -4.5V$	
On-State Drain Current	I <sub>D(ON)</sub>	-3	_	_	A	$V_{DS} \le -5V, V_{GS} = -2.5V$	
Gate-Source Leakage	I <sub>GSS</sub>	_	_	±80	nA	$V_{GS} = \pm 12V$ , $V_{DS} = 0V$	
ON CHARACTERISTICS (Note 5)							
Gate Threshold Voltage	V <sub>GS(th)</sub>	-0.45	_	-1.25	V	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	
Static Drain-Source On-Resistance	R <sub>DS (ON)</sub>	_	80	110	mΩ	$V_{GS} = -4.5V, I_D = -2.6A$	
Static Diain-Source On-Resistance			165	225	1112.2	$V_{GS} = -2.5V, I_D = -2.0A$	
Forward Transfer Admittance	Y <sub>fs</sub>	_	4	_	S	$V_{DS} = -5V, I_{D} = -2.6A$	
Diode Forward Voltage (Note 5)	$V_{SD}$	_	_	-1.26	V	$V_{GS} = 0V, I_{S} = -2.6A$	
DYNAMIC CHARACTERISTICS							
Input Capacitance	C <sub>iss</sub>	_	250		pF	101/1/	
Output Capacitance	Coss		88		pF	$V_{DS} = -10V, V_{GS} = 0V$ f = 1.0MHz	
Reverse Transfer Capacitance	$C_{rss}$	_	58		pF	1 = 1.001112	
Gate Resistance	$R_g$	_	12	16	Ω	$V_{GS} = 0V$ , $V_{DS} = 0V$ , $f = 1MHz$	
Total Gate Charge	Qg	_	4.3	5.3		V 45V V 40V	
Gate-Source Charge	Q <sub>gs</sub>	_	0.9		nC	$V_{GS} = -4.5V, V_{DS} = -10V,$	
Gate-Drain Charge	$Q_{gd}$	_	2.1			$I_D = -2.7A$	

Notes: 5. Short duration pulse test used to minimize self-heating effect.







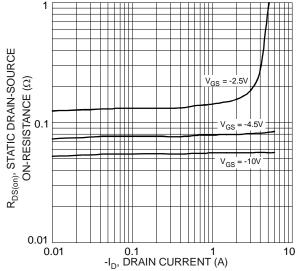


Fig. 3 On-Resistance vs. Drain Current and Gate Voltage

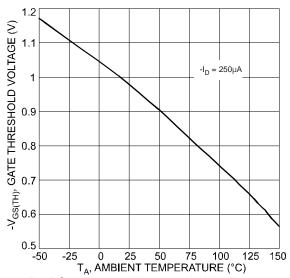


Fig. 5 Gate Threshold Voltage vs. Ambient Temperature

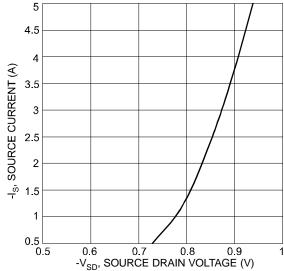
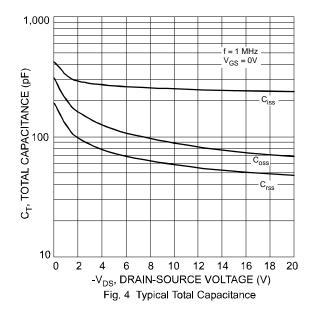


Fig. 7 Reverse Drain Current vs. Source-Drain Voltage



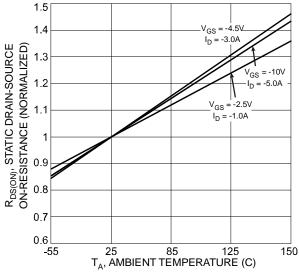


Fig. 6 Normalized Static Drain-Source On-Resistance vs. Ambient Temperature

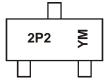


### Ordering Information (Note 6)

Part Number	Case	Packaging		
DMP2225L-7	SOT-23	3000/Tape & Reel		

Notes: 6. For packaging details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

## **Marking Information**



2P2 = Product Type Marking Code YM = Date Code Marking

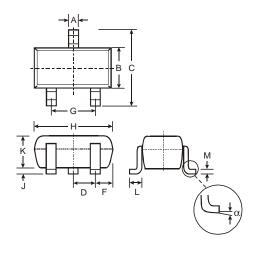
Y = Year (ex: V = 2008)

M = Month (ex: 9 = September)

Date Code Key

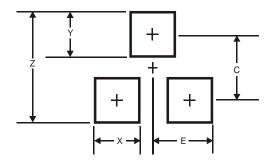
Date Code Ite												
Year	2008		2009	2010		2011	2012	:	2013	2014		2015
Code	V		W	Х		Υ	Z		Α	В		С
Month	Jan	Feb	Mar	Apr	Ma	y Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D

## **Package Outline Dimensions**



SOT-23					
Dim	Min	Max			
Α	0.37	0.51			
В	1.20	1.40			
С	2.30	2.50			
D	0.89	1.03			
F	0.45	0.60			
G	1.78	2.05			
Н	2.80	3.00			
J	0.013	0.10			
K	0.903	1.10			
L	0.45	0.61			
М	0.085	0.180			
α	0°	8°			
All Dimensions in mm					

# **Suggested Pad Layout**



Dimensions	Value (in mm)
Z	2.9
Х	0.8
Υ	0.9
С	2.0
E	1.35



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  - 2. support or sustain life and whose failure to perform when properly used in accordance with instructions for use provided in the labeling can be reasonably expected to result in significant injury to the user.
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